JST04W-600TW 1A TRIAC

Rev.A.1.1

The JST04W-600TW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST04W-600TW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. Package SOT-223-2L is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM} /V_{RRM}	600	V

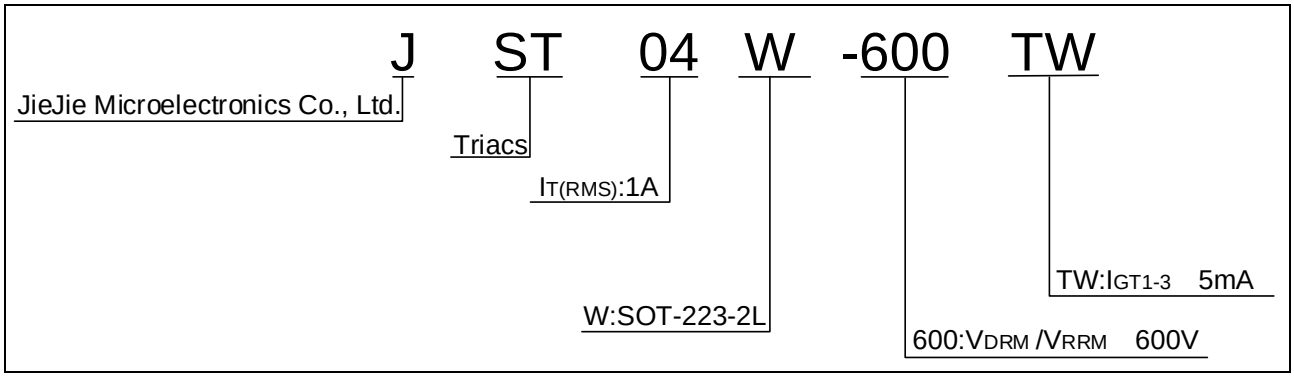
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Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	600	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	600	V
RMS on-state current (T_C 102)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)	I_{TSM}	25	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)		27.5	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	3.1	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT} , f=100Hz , T_j=125)	dI/dt	50	A/μs
Peak gate current (t_p=20μs , T_j=125)	I_{GM}	2	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	5	W

Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	4	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	N Tw 2.25 0 Td [1.8/P <</MCI9.5Tc 0 Tw 2.16 0 Td [(		


J
ST
04
W
-600
TW
JieJie Microelectronics Co., Ltd.
Triacs
IT(RMS):1A
W:SOT-223-2L
600:VDRM /VRRM 600V
TW:IGT1-3 5mA

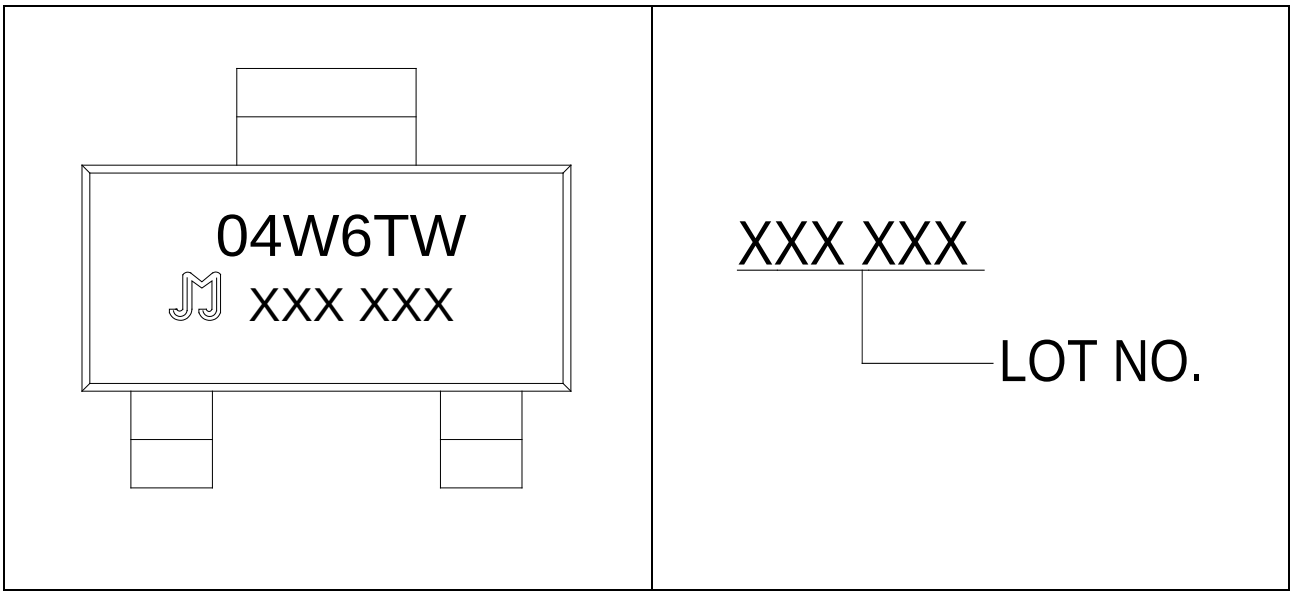

04W6TW
XXX XXX
XXX XXX
LOT NO.

FIG.1: Maximum power dissipation versus RMS on-state current

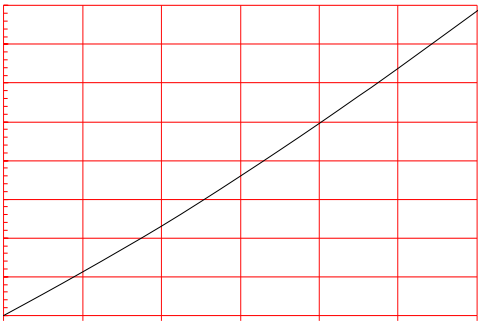


FIG.2: RMS on-state current versus case temperature

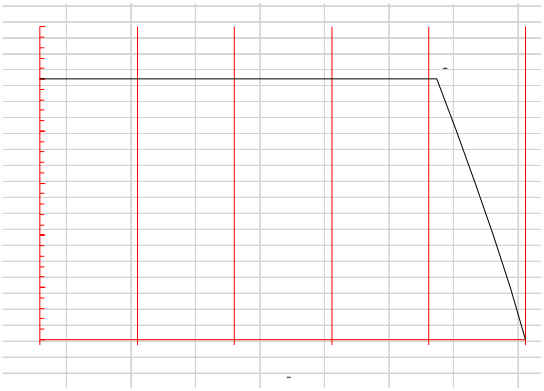


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

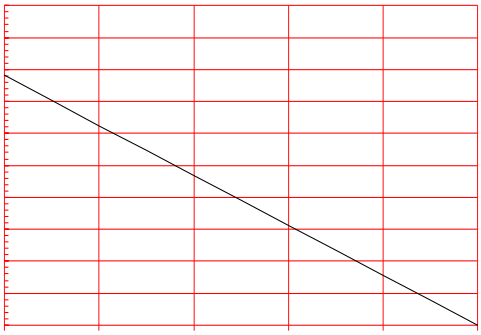


FIG.4: Surge peak on-state current versus number of cycles

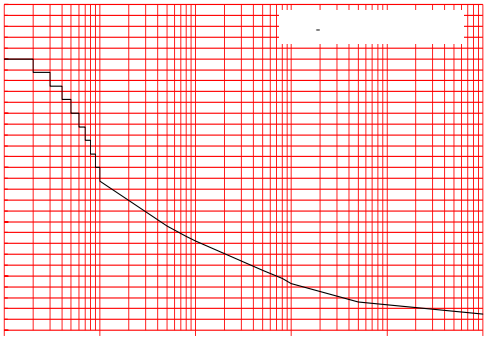


FIG.5: On-state characteristics

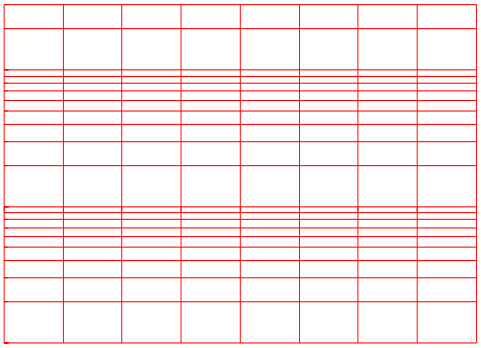


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<50A/μs)

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

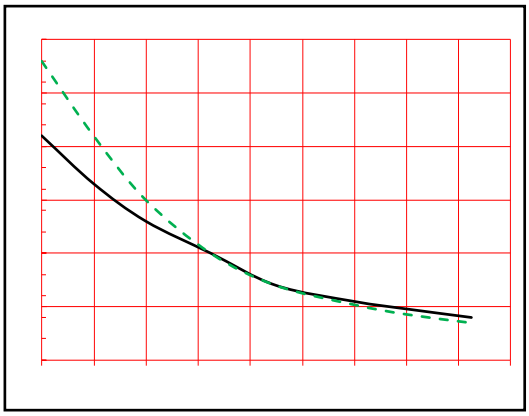
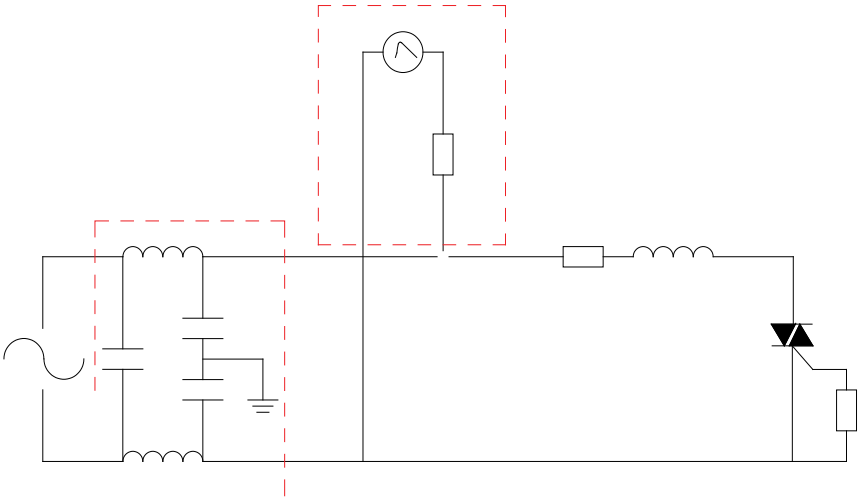
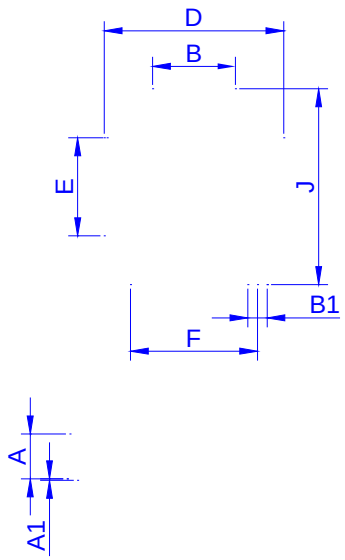
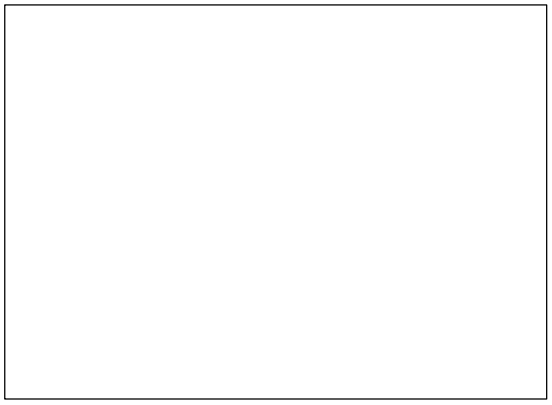
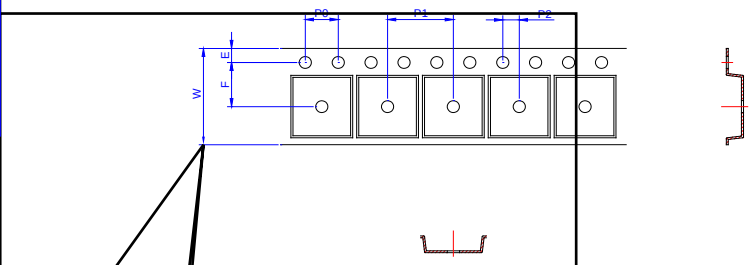


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards




D
B
E
J
B1
F
A
A1





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012